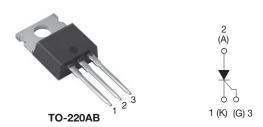


## VS-16TTS...PbF Series, VS-16TTS...-M3 Series

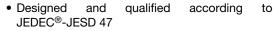
Vishay Semiconductors

# Thyristor High Voltage, Phase Control SCR, 16 A



PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub> 10 A					
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V				
V <sub>TM</sub>	1.4 V				
I <sub>GT</sub>	60 mA				
TJ	-40 °C to 125 °C				
Package TO-220AB					
Circuit configuration	Single SCR				

#### **FEATURES**





• 125 °C max. operating junction temperature

n temperature Co

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



## **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

#### **DESCRIPTION**

The VS-16TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operating up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS						
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS						
Capacitive input filter T <sub>A</sub> = 55 °C, T <sub>J</sub> = 125 °C, common heatsink of 1 °C/W	°C, 13.5 17 A					

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I <sub>T(AV)</sub>	Sinusoidal waveform	10	Δ		
I <sub>RMS</sub>		16	Α		
V <sub>DRM</sub> /V <sub>RRM</sub>	Range (1)	800/1200	V		
I <sub>TSM</sub>		200	А		
V <sub>T</sub>	10 A, T <sub>J</sub> = 25 °C	1.4	V		
dV/dt		500	V/µs		
dl/dt		150	A/µs		
T <sub>J</sub>	Range	-40 to 125	°C		

#### Note

<sup>(1)</sup> For higher voltage up to 1600 V contact factory

VOLTAGE RATINGS							
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA				
VS-16TTS08PbF, VS-16TTS08-M3	800	800	10				
VS-16TTS12PbF, VS-16TTS12-M3	1200	1200	10				



# VS-16TTS...PbF Series, VS-16TTS...-M3 Series

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ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL		TEST CONDITIONS	VALUES		UNITS		
PANAMETEN	STWIBOL TEST CONDITIONS		TYP.	MAX.	UNITS			
Maximum average on-state current	$I_{T(AV)}$	T <sub>C</sub> = 98 °C, 1	80° conduction, half sine wave	1	0			
Maximum RMS on-state current	I <sub>RMS</sub>			1	6	Α		
Maximum peak, one-cycle,	<b>L</b>	10 ms sine p	ulse, rated V <sub>RRM</sub> applied	1	70	Α .		
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine p	ulse, no voltage reapplied	20	00			
Maximum I <sup>2</sup> t for fusing	I <sup>2</sup> t	10 ms sine p	ulse, rated V <sub>RRM</sub> applied	144	A <sup>2</sup> s			
iviaximum i-t for fusing	1-1	10 ms sine pulse, no voltage reapplied		200		A-2		
Maximum I <sup>2</sup> √t for fusing	l²√t	t = 0.1 to 10 r	ns, no voltage reapplied	2000		A²√s		
Maximum on-state voltage drop	$V_{TM}$	10 A, T <sub>J</sub> = 25 °C		= 25 °C 1.4		٧		
On-state slope resistance	r <sub>t</sub>	T <sub>J</sub> = 125 °C		24	1.0	mΩ		
Threshold voltage	V <sub>T(TO)</sub>	] IJ= 125 0		1	.1	V		
Maximum reverse and direct leakage current	1 /1	T <sub>J</sub> = 25 °C	V - Botod V A	0	.5			
waximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	T <sub>J</sub> = 125 °C	$V_R = Rated V_{RRM}/V_{DRM}$	1	0			
Holding current	l <sub>Η</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A 16TTS08PbF, 16TTS12PbF, $T_J$ = 25 °C		ı	150	mA		
Maximum latching current	IL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C		Anode supply = 6 V, resistive load, $T_J = 25 ^{\circ}\text{C}$		20	00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max., linear to 80 °C, $V_{DRM} = R_g$ - k = Open		$T_J = T_J \text{ max., linear to } 80 ^{\circ}\text{C, } V_{DRM} = R_g - k = \text{Open}$		50	00	V/µs
Maximum rate of rise of turned-on current	dI/dt				50	A/μs		

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum peak gate power	$P_{GM}$		8.0	W		
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV		
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α		
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	٧		
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	90	mA		
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	60			
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	35			
Manipulation of BC and a		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	3.0			
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	V		
voltage to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V		
Maximum DC gate voltage not to trigger	$V_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value	0.25			
Maximum DC gate current not to trigger	$I_{GD}$	1j = 125 G, v <sub>DRM</sub> = nated value	2.0	mA		

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9			
Typical reverse recovery time	t <sub>rr</sub>	T. – 105 °C	4	μs		
Typical turn-off time	tq	T <sub>J</sub> = 125 °C	110			



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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-40 to 125	°C	
Maximum thermal resistance, junction to case		$R_{\text{thJC}}$	DC operation	1.3		
Maximum thermal resistance, junction to ambient		$R_{\text{thJA}}$		62	°C/W	
Typical thermal resistance, case to heatsink		$R_{thCS}$	Mounting surface, smooth and greased	0.5		
Approximate weight				2	g	
Approximate weight				0.07	OZ.	
Mounting torque	minimum			6 (5)	kgf · cm	
	maximum			12 (10)	(lbf $\cdot$ in)	
Marking davise			Coop at the TO 200AB	16TTS08		
Marking device		Case style TO-220AB		16TTS12		

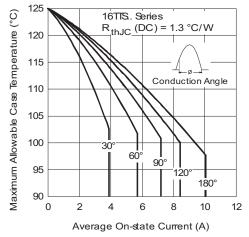


Fig. 1 - Current Rating Characteristics

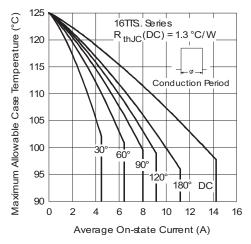


Fig. 2 - Current Rating Characteristics

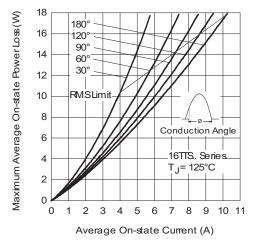


Fig. 3 - On-State Power Loss Characteristics

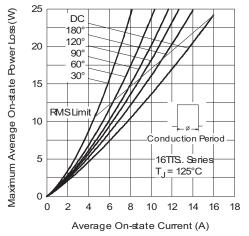


Fig. 4 - On-State Power Loss Characteristics

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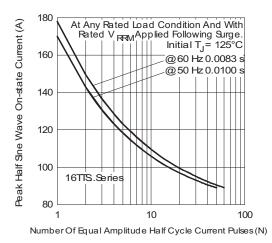


Fig. 5 - Maximum Non-Repetitive Surge Current

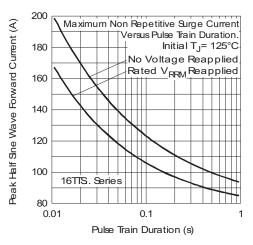


Fig. 6 - Maximum Non-Repetitive Surge Current

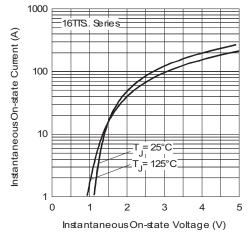


Fig. 7 - On-State Voltage Drop Characteristics

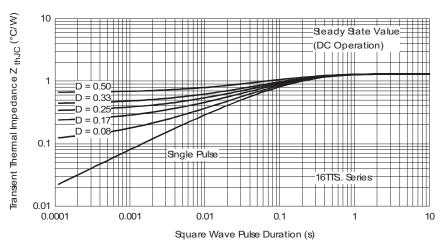


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

# VS-16TTS...PbF Series, VS-16TTS...-M3 Series

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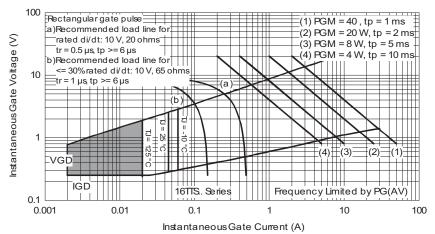
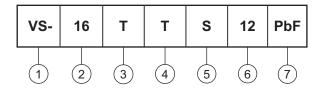


Fig. 9 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current rating

3 - Circuit configuration:

T = Single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

S = Converter grade

6 - Voltage code x 100 = V<sub>RRM</sub> - 08 = 800 V 12 = 1200 V

7 - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-16TTS08PbF	50	1000	Antistatic plastic tubes			
VS-16TTS08-M3	50	1000	Antistatic plastic tubes			
VS-16TTS12PbF	50	1000	Antistatic plastic tubes			
VS-16TTS12-M3	50	1000	Antistatic plastic tubes			

LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?95222				
Dort marking information	TO-220AB PbF	www.vishay.com/doc?95225		
Part marking information	TO-220AB -M3	www.vishay.com/doc?95028		



## Vishay Semiconductors

## **TO-220AB**

#### **DIMENSIONS** in millimeters and inches



## Lead assignments

## **Diodes**

- 1. Anode/open
- 2. Cathode
- 3. Anode

#### Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	IIN. MAX.		MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIM	IETERS	IETERS INCHES		NOTES
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° t	o 93°	
		•	•	•	

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

Lead tip



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